



life.augmented

Wire bonding: a thorough numerical methodology

Presenter

Beatrice Carasi

Authors

Beatrice Carasi, Lucrezia Guarino, Lucia Zullino, Luca Cecchetto

Agenda



Company presentation



Wire bonding



Model hypothesis and set up



Defining material properties
with simulations



Displacement and force
controlled simulations



Conclusion



Further points of discussion



STMicroelectronics

We are creators and makers of technology



One of the world's largest semiconductor companies



Over **50,000** employees
of which **9,000+** in R&D



\$16.1 billion revenues
in 2022



Over **80** sales & marketing
offices serving over **200,000**
customers across the globe

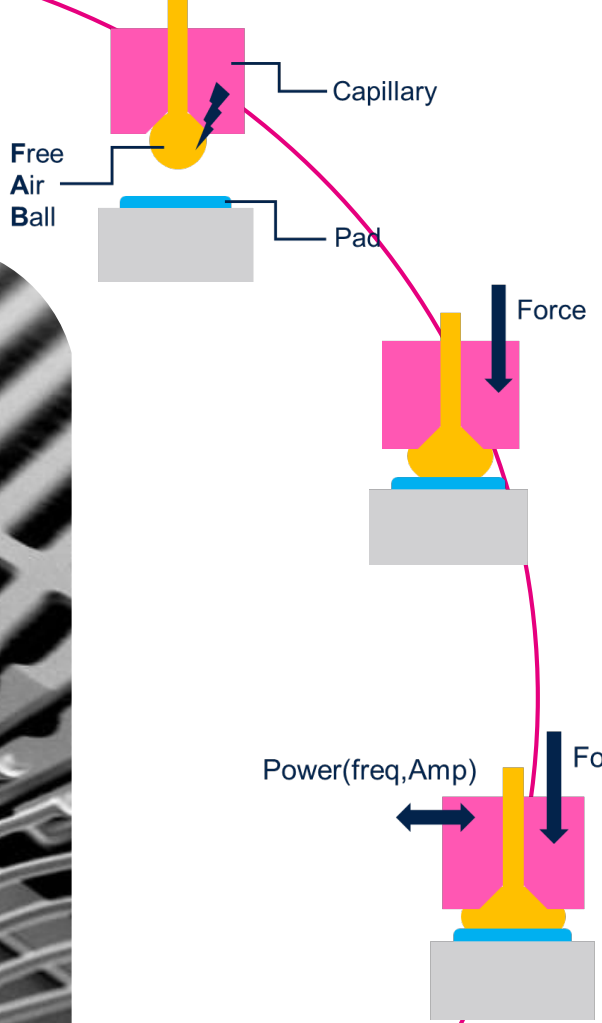
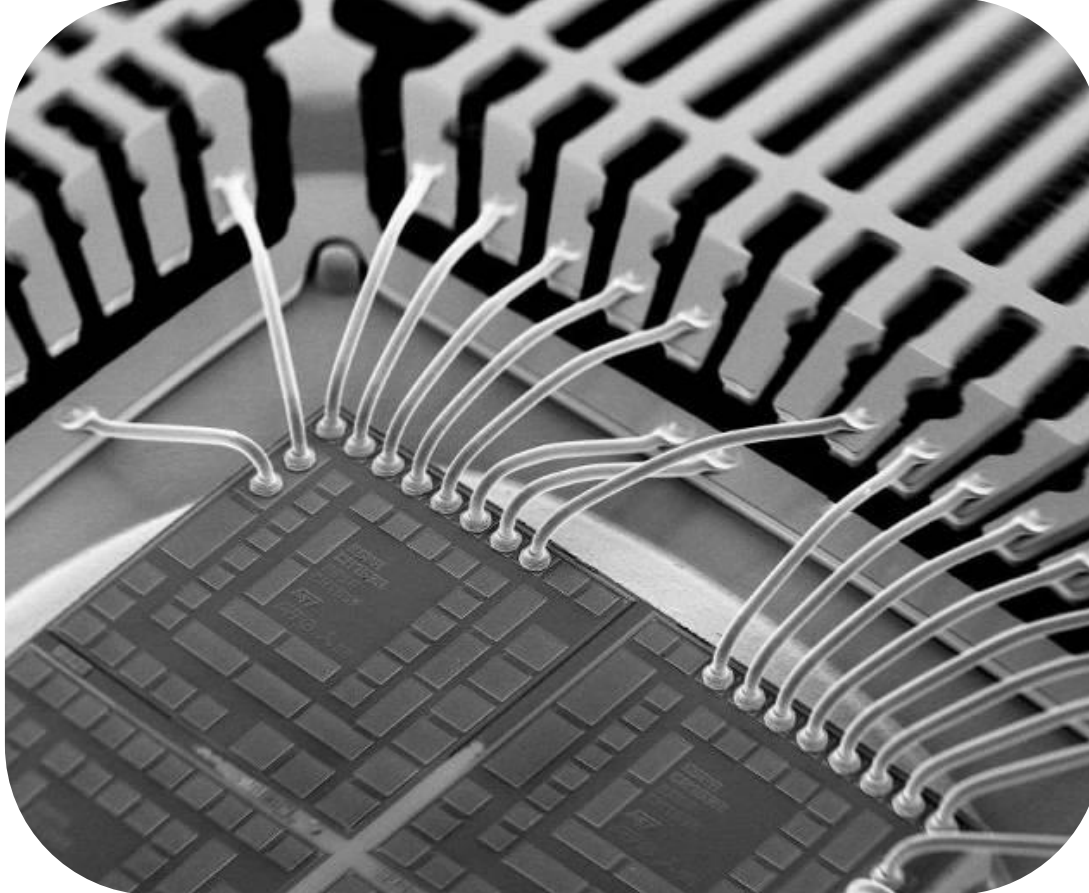


14 main manufacturing
sites



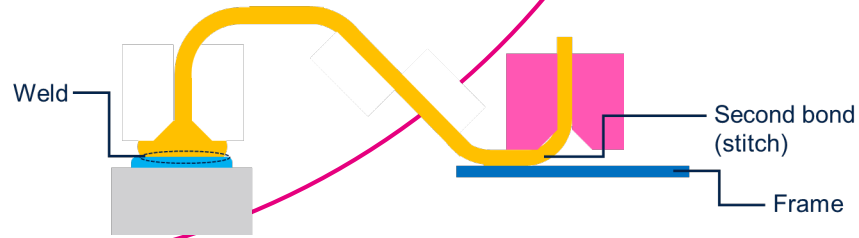
Signatory of the United Nations Global Compact (UNGC)
Member of the Responsible Business Alliance (RBA)

Wire bonding

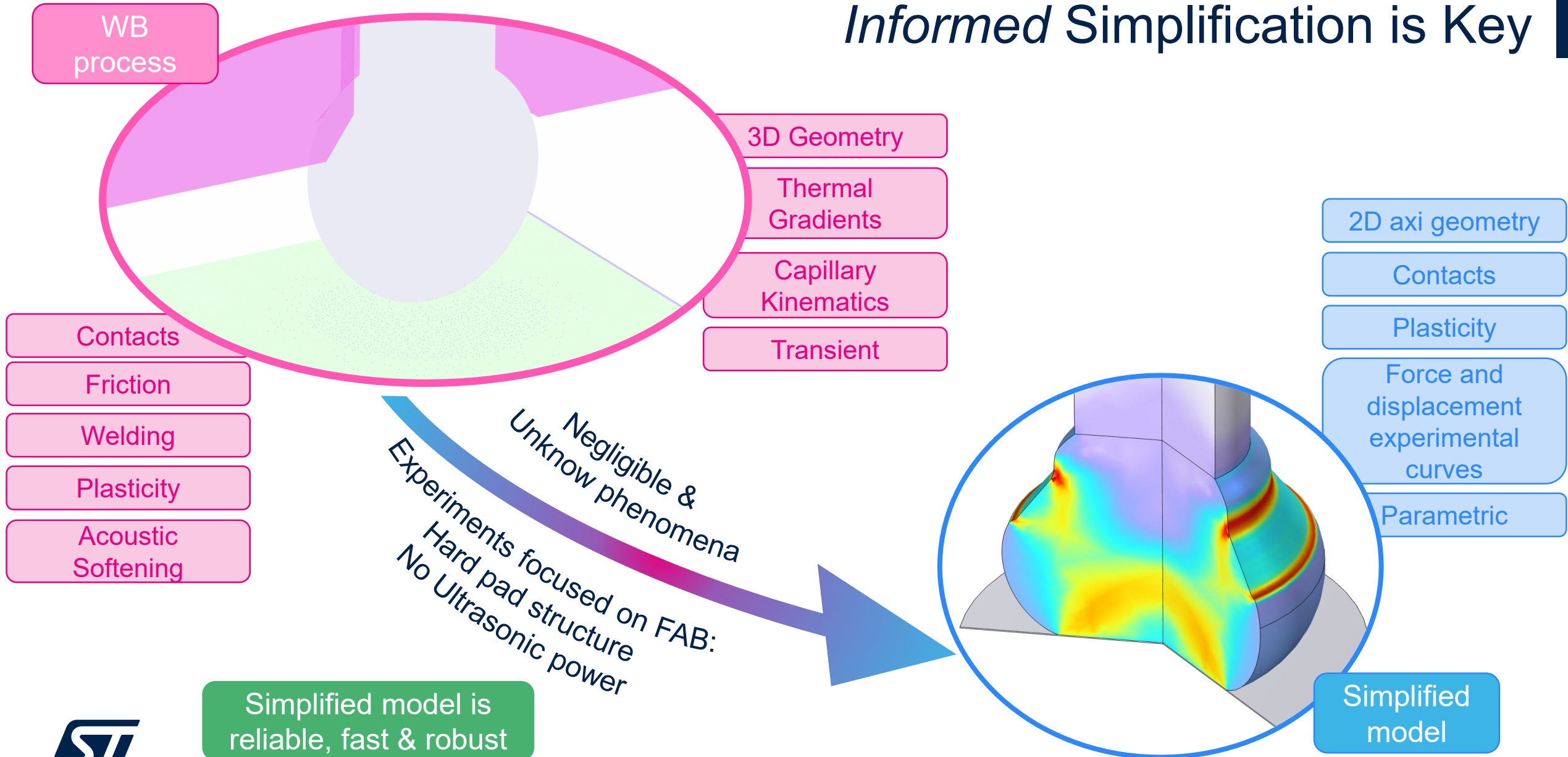


Wire bonding is a critical step in the chip packaging process since it can damage pads inducing cracks in dielectric layers.

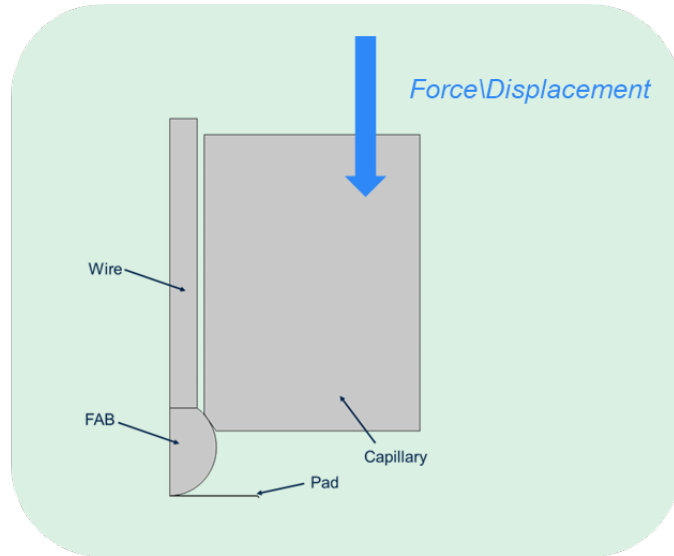
A robust numerical model is a key factor to anticipate manufacturing risks.



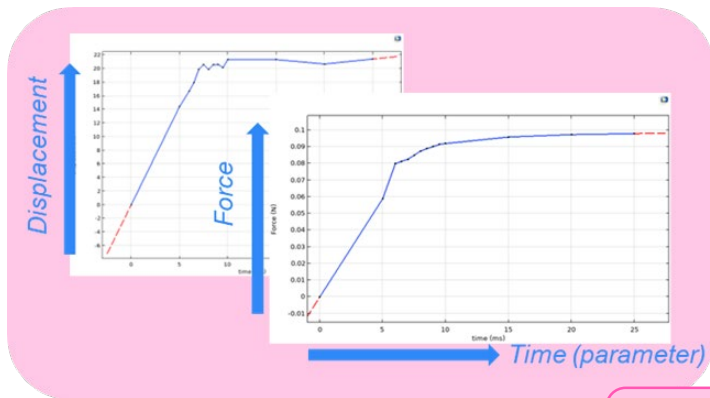
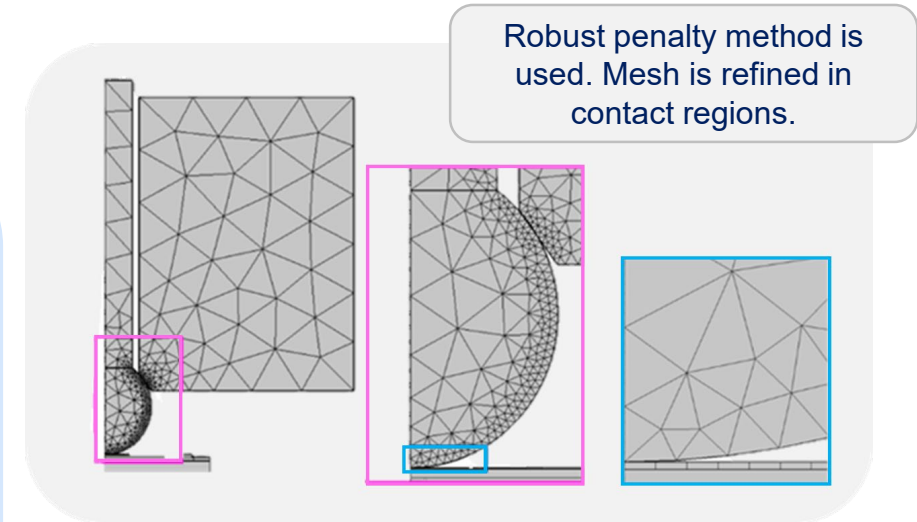
Model hypothesis and set up: *Informed Simplification is Key*



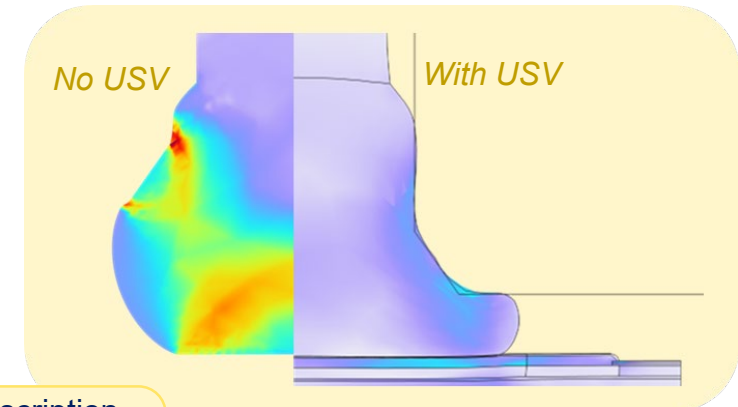
Model hypothesis and set up: The simplified model



- ☰ Solid Mechanics (solid)
 - ▣ Linear Elastic Material 1
 - ▣ Axial Symmetry 1
 - ▣ Free 1
 - ▣ Initial Values 1
 - ▣ Contact 1
 - ▣ Hyperelastic Material 1
 - ▣ Plasticity 1
 - ▣ Fixed Constraint 1
 - ▣ Rigid Material 1
 - ☰ Initial Values 1
 - ▣ Prescribed Displacement/Rotation



Experimental curves imposed on the capillary



Hyperelastic description more robust with high mesh deformations (important with USV)

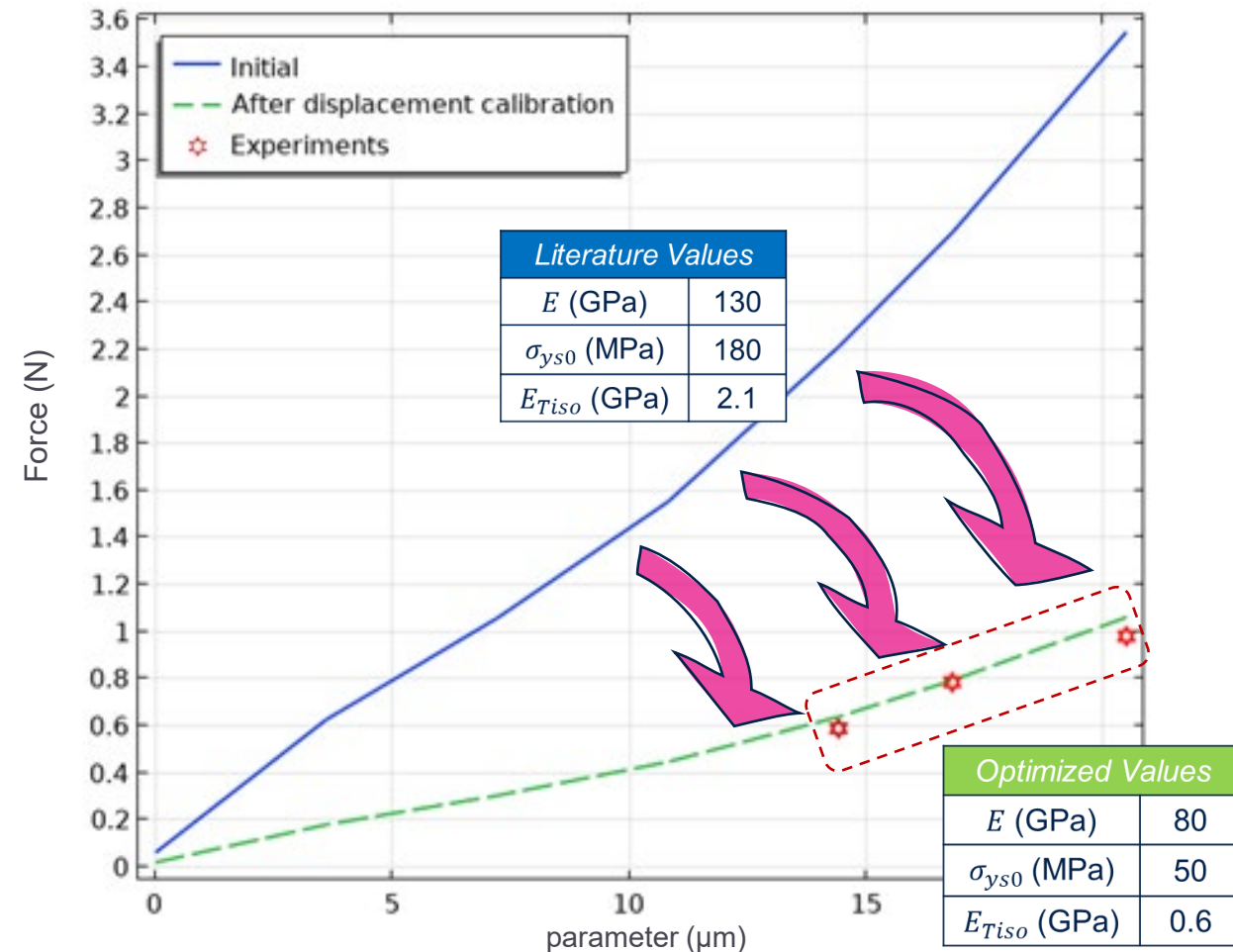
Defining material properties with simulations

Material properties of the FAB are not available and not easily to obtain experimentally.

Experimental TD (touch down, displacement) and force on the capillary are available.

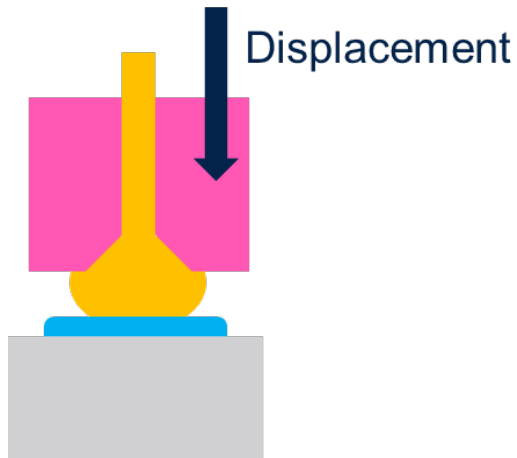
The constitutive law is captured correctly when both experimental displacement and force are matched. Material properties are scanned parametrically until this condition is reached.

This approach is valid not only for solid mechanics



Final displacement for 3 different forces is recorded in the experiments. Displacement controlled simulations. E is the Young's modulus, σ_{ys0} is the Initial yield stress and E_{Tiso} the isotropic tangent modulus

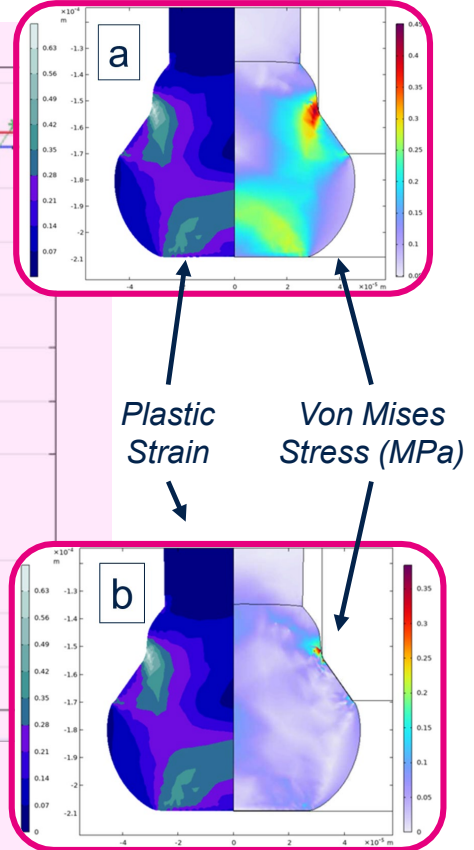
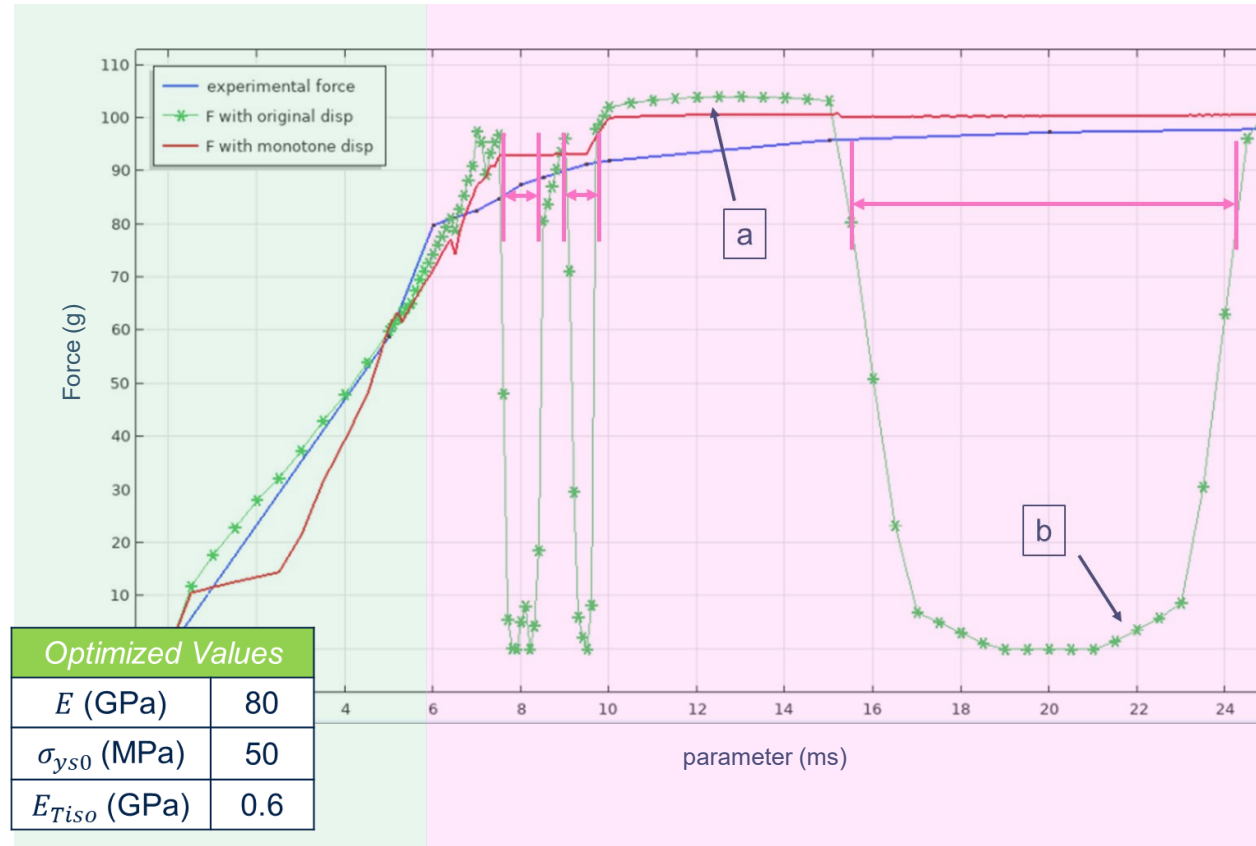
Displacement controlled simulations



A two segments bond is simulated.

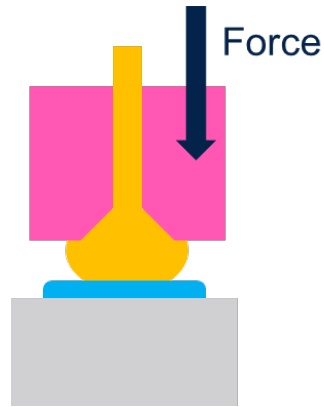
Force matching is good, this proves the correctness of the approach for identifying material properties.

First segment → → Second segment



The force drops to zero when the capillary is lifted from the plasticized ball.

Force controlled simulations

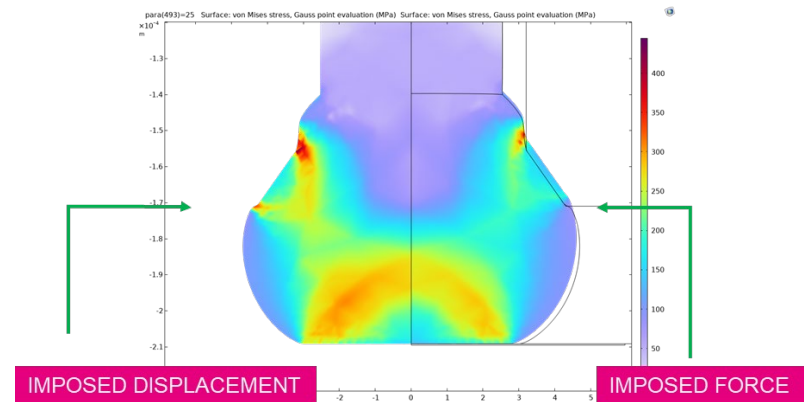
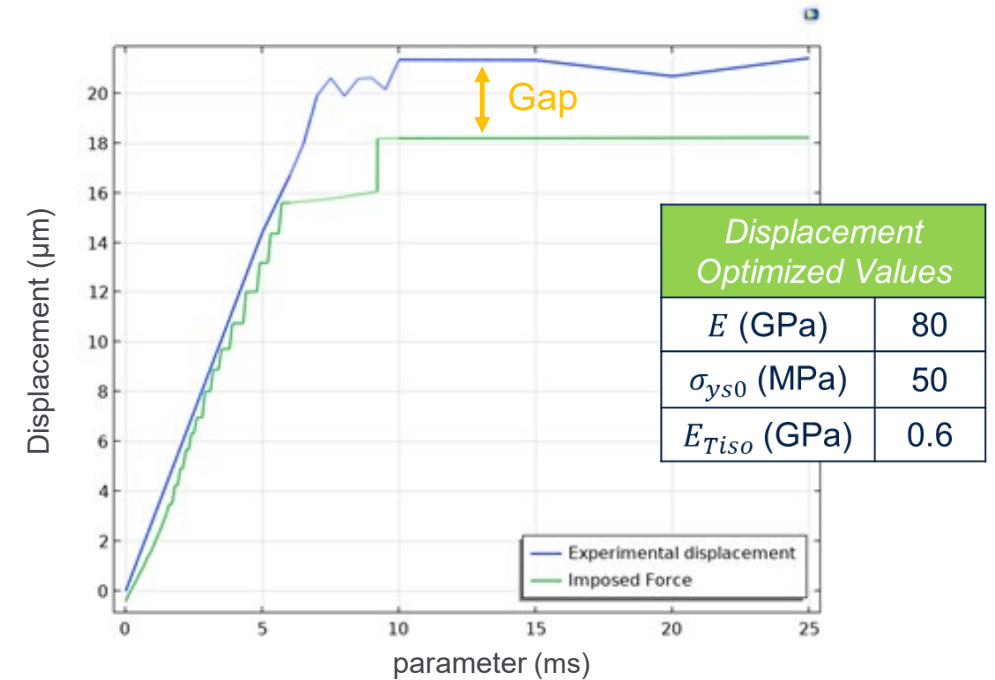


With the same material data that properly match the force imposing the TD, underestimation of the TD is observed imposing the force.



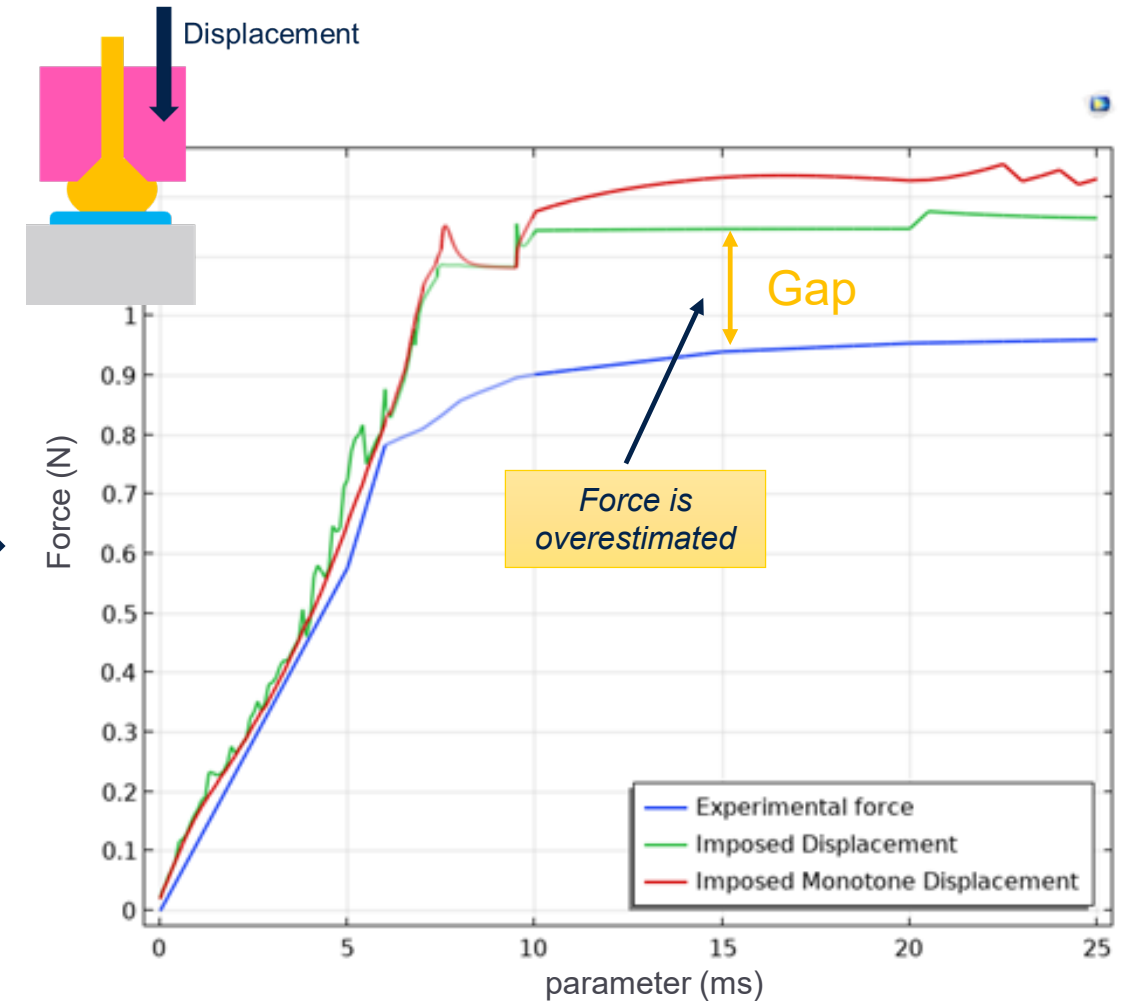
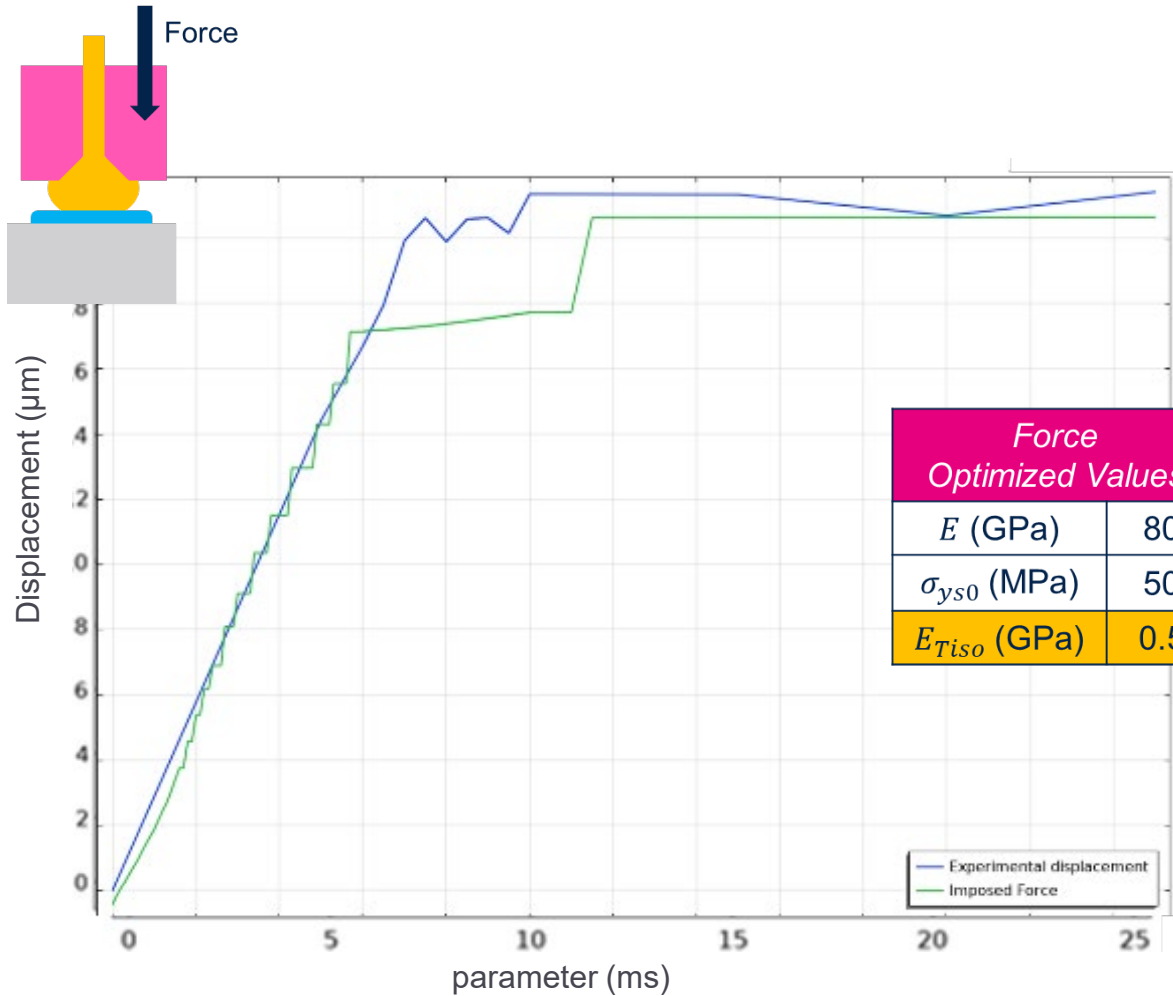
Both strategies should provide the same results, but this is true only if the physics of the system is fully understood*.

*capillary kinematics, material damping.... are unknown



Final deformation for two segments simulation

Force controlled calibration



Force and Displacement calibration produce slightly different optimal material parameters.

Displacement vs Force controlled simulations

We have seen that, with respect to matching experimental data, either force and displacement controlled provide good (even if different) results.

u

Displacement controlled

- Easier to constrain in static simulations
- Numerically more robust (default Double Dogleg non-linear solver)

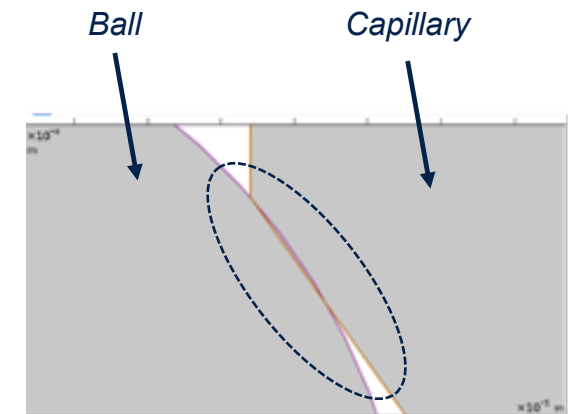


More robust and faster. Should be preferred when possible.

F

Force controlled

- Strategies for a well posed\constrained numerical model are needed (spring foundations or other*)
- Non-linear solver is changed from the default to the more 'cautious' constant Newton, with 0.1 as damping factor.



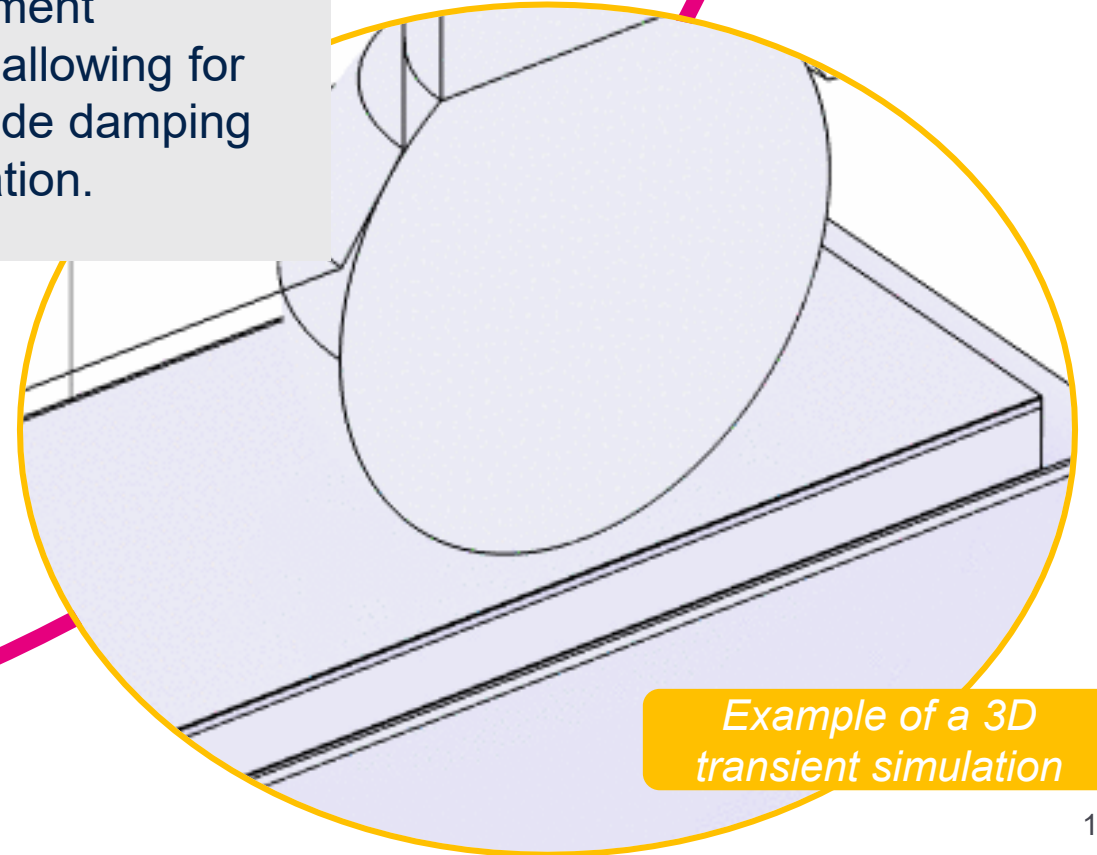
*In 2D axi, a constraint is missing in the vertical direction if the force is imposed. An initial interference between ball and capillary is used to resolve this at t=0.

Conclusion

- Numerical simulations, combined with experimental data, can be used to infer material properties
- Displacement controlled and force controlled capillary movement produce slightly different results since kinematic of the piezoelectric actuator is unknown.
- Displacement is, as expected, to be preferred as more robust numerical input with respect to force.

Future enhancements

- model ball-pad adhesion
- when acoustic softening is present, control the horizontal capillary displacement imposing a force, allowing for oscillation amplitude damping due to weld formation.



Example of a 3D transient simulation

Further points of discussion

- 2D axisymmetric
 - transient analysis provided better match in the two segments transition zone but it is of course much slower
 - can be used as a *first* screening test for material properties characterization even in presence of USV, since most of the phenomenon is the softening of the material (lateral translation affects more ball\pad interface)
 - The Ludwik model describes better the stress-strain behavior with USV (high deformation)
- 3D are the goal since different pad structure are to be analyzed
 - Harder to constrain than 2D axisymmetric
 - Much slower (from tens of minutes to hours of computation)
 - Quadratic elements are paramount to be able to describe the shape of the ball at high TD
-

No temperature gradients because only the FAB is non rigid and the stress-strain curve is at that temperature

Wire bonding: a thorough numerical methodology

B. Carasi, L. Gasario, L. Zullino, L. Cecchetto
STMicronics srl
via C. Olivetti, 2, 20864 Agrate Brianza (MB), Italy
Email: beatrice.carasi@st.com, lucrezia.gasario@st.com, luca.zullino@st.com, luca.cecchetto@st.com

Abstract

The semiconductor industry is always looking for early anticipation of manufacturing risks, pushing the development of Computer Aided Engineering (CAE) modeling of processes. Robust Chip-Package Interaction (CPI) design requires a deep understanding of thermo-mechanical stresses imposed during the assembly process; one of the critical steps is wire bonding, which can damage pads inducing cracks in dielectric layers. Aim of this paper is the investigation of an appropriate simulation strategy, using COMSOL Multiphysics, of a 3D thermo-mechanical model of thermo-sonic wire bonding, that represents the physics accurately but also seeks numerical robustness, starting from appropriately simplified models. How numerical analysis together with experimental data can be used to obtain mechanical material characterization for thin/high temperature copper wires is also shown.

1. Introduction

1.1 The wire bonding process
All dielectric devices are packaged on silicon die. Packaging is necessary to protect the device from the environment and connect it with its application. There are many ways to achieve electrical interconnection and wire bonding (WB) is one of the alternatives (others are, for example, solder balls and direct copper interconnection). Wire bonding (see Figure 1) consists on the formation of a free air ball (FAB) at the tip of a metal wire constrained and moved by a capillary. A spark melts the wire and then the ball is pushed on the chip pad and oscillated. When the bond between ball and pad is formed the capillary lifts and translates. The wire forms a loop and then gets snatched to the package side of the connection and cut (Figure 2). This paper focuses on the first part of the process i.e. the ball-pad connection. This is the most critical one, with respect to structural assessment, since it is the die that contains functional ingredients that need to maintain their integrity during the bonding process. Also, the wire-pad interface needs to be strong enough to stay in place during operational lifetime of the chip and provide an appropriate electrical connection area. Inputs of the first bond process (and so of the numerical model) are the *temperature*, the *vertical force* on the capillary and the *ultrasonic (US) power* (combination of oscillation frequency and amplitude of the capillary tool) at each step of the process (segment). Multiple segments are possible depending on the product specifics. Many factors, including

material properties of the involved surfaces [1], influence the solid state weld that is formed.



Figure 1. Wire bonding process. 1. electrical spark, 2. vertical force application, 3. ultrasonic vibration.

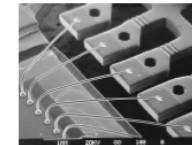


Figure 2. First (chip) and second (frame) bonds.

1.2 The numerical model

The purpose of a numerical model for wire bonding is to provide feedback both to front end (chip) design and back end (packaging) process. With it, different material stacks, routing and bonding process parameters can be explored [2]. It will be shown that numerical models can be used to infer material characterization, provided that experimental data are available. Translation onto a mathematical model of the process described in chapter 1.1 can reach different degrees of accuracy (and numerical complexity). A somewhat complete description of WB would be a 3D, transient, structural mechanics model with contacts, non-linear materials, surface friction and stick criterion to describe welding, accounting for thermal gradients in the structure and, as it will be evident, a proper knowledge of the ultrasonic transducer kinematic behavior. It is well understood, in the simulation community, that a correctly simplified model can be of great insight and constitutes fundamental numerical foundation to build more complete ones.

1.2.1 Numerical models as characterization tools

Thermo-sonic wire bonding is a process in which the wire (here copper) is oscillated at ultrasonic frequency (50-150 kHz) inducing a softening of the metal called acoustic softening effect [3]. This, combined with a high temperature (220°C in our investigated case), softens the material during bonding. Setting up an experiment to characterize the non-linear, plastic behavior would require dedicated equipment with in-situ ultrasonic oscillation capabilities.

Find more details in our paper



Our technology starts with You



Find out more at www.st.com

© STMicroelectronics - All rights reserved.

ST logo is a trademark or a registered trademark of STMicroelectronics International NV or its affiliates in the EU and/or other countries.

For additional information about ST trademarks, please refer to www.st.com/trademarks.

All other product or service names are the property of their respective owners.



life.augmented